UTC 2SA1201 PNP EPITAXIAL SILICON TRANSISTOR

SILICON PNP EPITAXIAL **TRANSISTOR**

DESCRIPTION

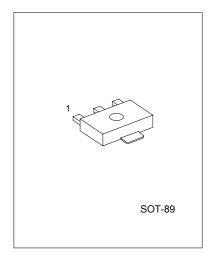
The UTC 2SA1201 is designed for power amplifier and voltage amplifier applications.

FEATURES

*High voltage: VcEo= -120V

*High transition frequency: f_T=120MHz(typ.)

*Pc=1 to 2 W(mounted on ceramic substrate)



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| PARAMETER | SYMBOL VALUE | | UNIT | | | |
|-----------------------------|--------------|------------|------|--|--|--|
| Collector-Base Voltage | Vсво | -120 | V | | | |
| Collector-Emitter Voltage | VCEO | -120 | V | | | |
| Emitter-Base Voltage | VEBO | -5 | V | | | |
| Collector Current | lc | -800 | mA | | | |
| Base Current | Ів | -160 | mA | | | |
| Collector Power Dissipation | Pc | 500 | mW | | | |
| | Pc* | 1000 | mW | | | |
| Junction Temperature | Tj | 150 | °C | | | |
| Storage Temperature | Tstg | -55 ~ +150 | °C | | | |

^{*:} Mounted on cermic substrate(250mm² × 0.8t)

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

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|-----------------------------------|------------------|-------------------------------|------|-----|------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| Collector to emitter breakdown | V(BR)CEO | Ic= -10mA, IB=0 | -120 | | | V |
| voltage | | | | | | |
| Emitter to Base breakdown voltage | V(BR)EBO | IE= -1mA, IC=0 | -5 | | | V |
| Collector cut-off current | I _{CBO} | Vcb= -120V, I _E =0 | | | -0.1 | μА |
| Emitter cut-off current | I _{EBO} | VEB= -5V, I _C =0 | | | -0.1 | μΑ |
| DC Current Gain | h _{FE} | VCE= -5V, IC= -100mA | 80 | | 240 | |
| Collector to emitter saturation | VCE(sat) | Ic= -500mA, IB= -50mA | | | -1.0 | V |
| voltage | | | | | | |
| Base to emitter voltage | VBE | VCE= -5V, IC= -100mA | | | -1.0 | V |
| Transition frequency | fτ | Vce= -5V, Ic= -100mA | | 120 | | MHz |
| Collector output capacitance | Cob | VCB= -10V, IE=0, f=1MHz | | | 30 | pF |

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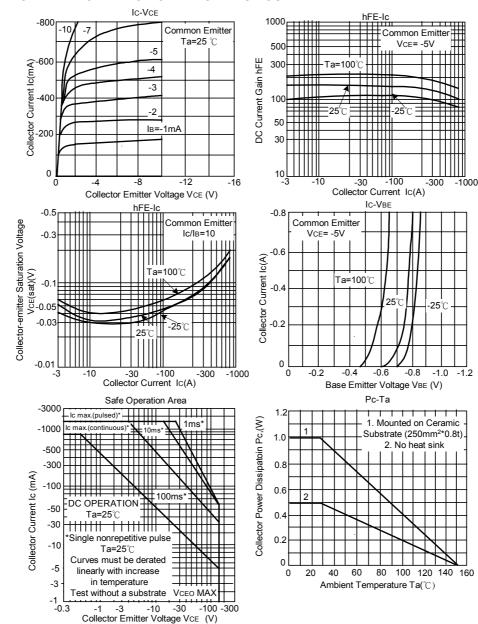
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CLASSIFICATION OF hFE

| RANK | 0 | Y |
|-------|----------|-----------|
| RANGE | 80 - 160 | 120 - 240 |

TYPICAL PERFORMANCE CHARACTERISTICS



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